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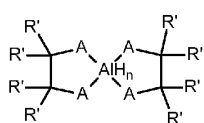
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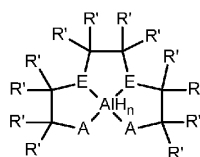
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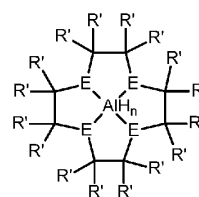
(54) Title: PROCESS FOR THE GENERATION OF METAL- OR SEMIMETAL-CONTAINING FILMS



(I)



(II)



(III)

(57) Abstract: The present invention is in the field of processes for preparing inorganic metal- or semimetal- containing films. The process comprising (a) depositing a metal- or semimetal-containing compound from the gaseous state onto a solid substrate and (b) bringing the solid substrate in contact with a compound of general formula (I), (II), or (III) in the gaseous state (I) (II) (III) wherein A is NR, NR₂, PR, PR₂, O, OR, S, or SR, E is N, NR, P, PR, O or S, n is 1, 2, or 3, R is an alkyl group, an alkenyl group, an aryl group, or a silyl group and R' is hydrogen, an alkyl group, an alkenyl group, an aryl group, or a silyl group, and A, E, and n are chosen such that the compound of general formula (I), (II), or (III) is electronically neutral.

